Electronic supplementary information of

Silicon nanocrystal hybrid photovoltaic devices for indoor light energy harvesting

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Figure S1. FTIR spectra of SiNCs before and after thermal annealing; as-H:SiNCs (no annealing), H:SiNCs (200 °C for 1 hour) and H:SiNCs (400 °C for 1 hour)
Figure S2. Deconvolution of SiHₙ bonds on the as-H:SiNC (no annealing) surface